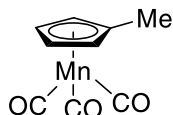


Catalog # 25-1550 Methylcyclopentadienylmanganese tricarbonyl, min. 97%



## Thermal Behavior:

- Melting point -2.2°C
- Boiling point 233°C

## Technical Notes:

1. Precursor used for manganese thin film deposition.

Target Deposit	Deposition Technique	Delivery Temperature	Pressure	Co-reactants	Deposition Temperature	Ref.
Mn	CVD, ALD	-	4.6×10 <sup>-4</sup> Torr	-	350-450°	1-2
MnO <sub>x</sub>	PE-CVD	50°C	0.4-0.7 Torr	500W plasma, O <sub>2</sub> :H <sub>2</sub>	30°C	3
MnP	CVD	-	40 Torr	<sup>t</sup> BuPH <sub>2</sub>	550-650°C	4
Zn <sub>1-x</sub> Mn <sub>x</sub> O	CVD	-	-	Et <sub>2</sub> Zn, O <sub>2</sub> , <sup>t</sup> BuOH	450°C	5

## References:

1. [J. Phys. Chem. C, 2012, 116, 23585.](#)
2. [Organometallics 2014, 33, 5308.](#)
3. [Thin Solid Films, 2014, 556, 28.](#)
4. [J. Appl. Phys. 2014, 116, 133512.](#)
5. [J. Appl. Phys. 2005, 97, 10D327.](#)